Supplemental Information:

Crosslinked and Dopant free Hole Transport Materials for

Efficient and Stable Planar Perovskite Solar Cells

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Material Synthesis:



Synthesis of DH-MeO-FDPA

A mixture of 2,7-dibromo-9,9-di(hex-5-en-1-yl)-9H-fluorene (500 mg, 1.11 mmol), bis(4-methoxyphenyl)amine (640 mg, 2.79 mmol), potssium tert-butoxide (375 mg, 3.35 mmol) and toluene (10 mL) was placed in a Schlenk flask. The mixture was carefully degassed before and after $Pd(OAc)_2$ (25 mg, 0.11 mmol) and tri-tert-butyl phosphine (23 mg, 0.11 mmol) was added. After stirred and refluxed for 12 h, the reaction was stopped. After cooling to room temperature, water was added to quench the reaction. The mixture was extracted with ethyl acetate, the organic layer was dried over anhydrous MgSO₄. After filtration, the organic solvent was moved under reduced pressure. The residue was further purified by silica gel column chromatography to give DH-MeO-FDPA (780 mg, yield 89%) as pale yellow solid.

¹H (d_6 -DMSO, 400 MHz) δ : 7.43 (d, J = 8.12 Hz, 2H), 6.83-6.94 (m, 18H), 6.70 (d, J = 8.04 Hz, 2H), 5.58-5.65 (m, 2H), 4.83-5.19 (m, 4H), 3.70 (s, 12H), 1.51-1.81 (m, 8H), 1.03-1.07 (m, 4H), 0.59-0.61 (m, 4H).



Fig. S1 Stability date of unencapsulated perovskite devices with crosslinked VB-MeO-FDPA and PEDOT:PSS HTMs under continuous one sun illumination in a N_2 box



Fig. S2 Current density-voltage (J–V) characteristics of hole-only devices with the structure of ITO/PEDOT:PSS/HTMs/MoO₃/Ag



Fig. S3 Contact angles of water on four HTMs a) MeO-FDPA, b) DH-MeO-FDPA, c) VB-MeO-FDPA and d) VB-Me-FDPA



Fig. S4 Statistic results of perovskite grain size coated on different hole transport layers.



Fig. S5 J-V curves of perovskite devices with various thickness of crosslinked HTM(VB-MeO-FDPA)



Fig. S6 SEM images of perovskite films deposited on different HTMs a) PEDOT:PSS, b) VB-MeO-FDPA and c) PEDOT:PSS/ VB-MeO-FDPA bilayer.

HTLs		Perovskite	PEDOT:PSS	MeO-FDPA	DH- MeO- FDPA	VB- MeO- FDPA	VB-Me- FDPA
PL lifetime /ns	$ au_1$	56.70	48.75	44.64	28.38	13.87	37.31
	τ ₂	13.27	15.15	15.84	13.17	5.08	10.49

Table. S1 Summarization of the PL decay time for perovskite films with differentHTLs.

Table. S2 Photovoltaic performance of PSCs with VB-MeO-FDPA treated at different crosslinking Temperature

Crosslinking	Temp	J_{sc} (mA/cm ²)	$V_{oc}\left(\mathbf{V}\right)$	FF (%)	PCE (%)
(°C)					
RT		5.4	0.78	19.4	0.8
100		12.6	1.01	50.2	6.4
140		17.9	0.96	64.5	11.1
160		20.9	1.15	77.5	18.7
200		19.8	1.09	74.0	16.0